

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of:

Atty. Docket No.: 002372.00043

KANAYA et al.

Serial No.: TBA

Group Art Unit: TBA

Filed: June 25, 2003

Examiner: TBA

For: Semiconductor Device Having Ferroelectric Capacitor and Hydrogen Barrier Film and Manufacturing Method Thereof

INFORMATION DISCLOSURE STATEMENT UNDER 37 C.F.R. § 1.97

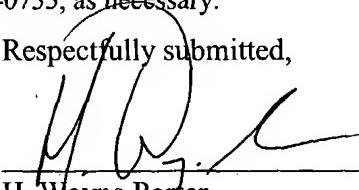
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

Applicants submit herewith the attached Form PTO/SB/08A. Pursuant to 37 C.F.R. § 1.98(d), Applicants have not submitted the references cited on the attached Form PTO/SB/08A with this paper. A copy of each reference can be found in the file of parent application Serial No. 09/570,026. Applicants respectfully request that the Examiner consider and enter all the documents cited on the enclosed Form PTO/SB/08A into the file of the above-identified application. Applicants also request an indication of the same by return of the Form PTO/SB/08A being initialed and dated by the Examiner.

No fees are believed due to ensure consideration of the attached documents by the Examiner. However, if any fees are required or an overpayment of fees made, the Commissioner is hereby authorized to debit or credit our Deposit Account No. 19-0733, as necessary.

Respectfully submitted,


H. Wayne Porter
Registration No. 42,084

Date: June 25, 2003

By:

BANNER & WITCOFF, LTD.
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(202) 824-3000
(202) 824-3001 (fax)

Attachments:

Form PTO/SB/08A

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PTO/SB/08A (08-00)

Approved for use through 10/31/2002. OMB 0651-0031

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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Sheet

1 of 2

Complete if Known

Application Number	TBA
Filing Date	June 25, 2003
First Named Inventor	Kanaya et al.
Group Art Unit	TBA
Examiner Name	TBA
Attorney Docket Number	002372.00043

U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code ² (if known)			
		5,185,689		MANIAR	02-09-1993	
		6,242,299		HICKERT	06-05-2001	
		6,316,801		AMANUMA	11-13-2001	

FOREIGN PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	Foreign Patent Document			Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ₆
		Office ³	Number ⁴	Kind Code ⁵ (if known)				
		WO	009735341		Hitachi Ltd.	09-25-1997		Abstr.
		JP	04-102367		Seiko Epson Corp.	04-03-1992		Abstr.
		JP	06-013346		Seiko Epson Corp.	01-21-1994		Abstr.
		JP	06-209113		Ramtron Intl. Corp.	07-26-1994		Abstr.
		JP	07-111318		Olympus Optical Co. Ltd.	04-25-1995		Abstr.
		JP	09-331031		NEC Corp.	12-22-1997		Abstr.
		JP	10-012830		Sony Corp.	01-16-1998		Abstr.
		JP	10-275897		Toshiba Corp.	10-13-1998		Abstr.
		JP	11-017124		Toshiba Corp.	01-22-1999		Abstr.
		JP	7-111318			4/1995		
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		JP	8-335673			12/1996		
		JP	9-331031			12/1997		
		JP	10-116965			5/1998		
		JP	10-255483			9/1998		

Examiner Signature	Date Considered
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹ Unique citation designation number. ² See attached Kinds of U.S. Patent Documents. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

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2

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Examiner Name	TBA

Attorney Docket Number 002372.00043

OTHER PRIOR ART -- NON PATENT LITERATURE DOCUMENTS			
Examiner Initials *	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
		N. TANABE, T. MATSUKI, S. SAITO, T. TAKEUCHI, S. KOBAYASHI, T. NAKAJIMA, Y. MAEJIMA, Y. HAYASHI, K. AMANUMA, T. HASE, Y. MIYASAKA AND T. KUNIO, A Ferroelectric Capacitor over Bit-line (F-COB) Cell for High Density Nonvolatile Ferroelectric Memories, 1995 Symposium on VLSI Technology Digest of Technical Papers, pp. 123-124, 0-7803-2602-4/95, Microelectronics Research Laboratories, Fundamental Research Laboratories, NEC Corporation 1120, Shimokuzawa, Sagamihara, Kanagawa 229, Japan	
		English Language Translation of Japanese Laid-Open Publication No. Hei 9-331031 1997, filed December 22, 1997 (translated by Hidetoshi Kitsuya, December 5, 2002).	
		T. MORIMOTO et al., "Excellent Ferroelectric Properties in PZT Capacitor Cell with Thin SRO Film in Both Top and Bottom Electrodes," Extended Abstracts of the 1999 International Conference on Solid State Devices and Materials, Tokyo, 1999 pp. 396-397.	

Examiner Signature	Date Considered
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